

Features

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-20V	14m Ω @-4.5V	-10A
	17m Ω @-2.5V	

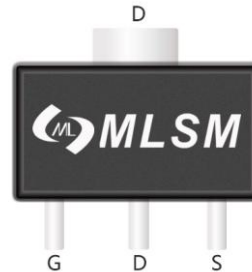
Application

- PWM applications
- Power management
- Load switch

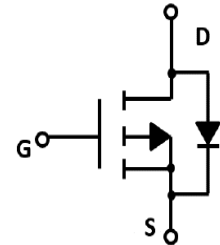


0C10AP : Device code
 XXXX : Code

Marking and pin assignment



SOT-89-3L top view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±12	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-10	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	-44	A
I _D	Continuous Drain Current	Tc=25°C	-10	A
P _D	Maximum Power Dissipation	T _A =25°C	1.7	W
R _{θJA}	Thermal Resistance Junction-to-Ambient		315	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MZ0C10AP	SOT-89-3L	0C10AP	1,000	10,000	40,000	7"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.5	--	-1.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-8A	--	14	18	mΩ
		V _{GS} =-2.5V, I _D =-5A	--	17	25	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	2700	--	pF
C _{OSS}	Output Capacitance		--	680	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	590	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-6V, I _D =-10A, V _{GS} =-4.5V	--	35	--	nC
Q _{gs}	Gate Source Charge		--	5	--	nC
Q _{gd}	Gate Drain Charge		--	10	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-1A, V _{GS} =-4.5V, R _G =10Ω	--	11	--	nS
t _r	Turn-on Rise Time		--	35	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30	--	nS
t _f	Turn-Off Fall Time		--	10	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =-10A	--	--	-1.2	V

Typical Operating Characteristics

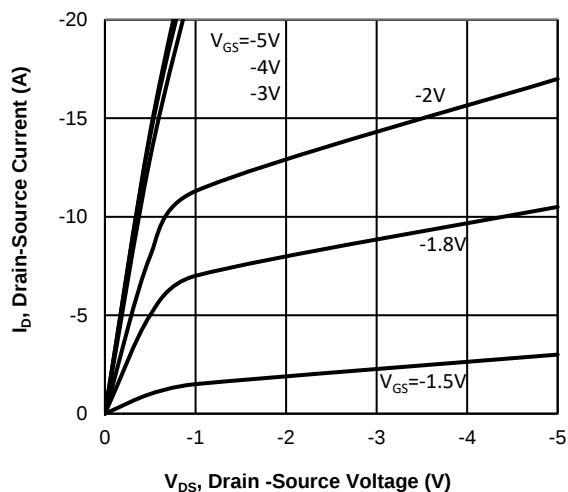


Fig1. Typical Output Characteristics

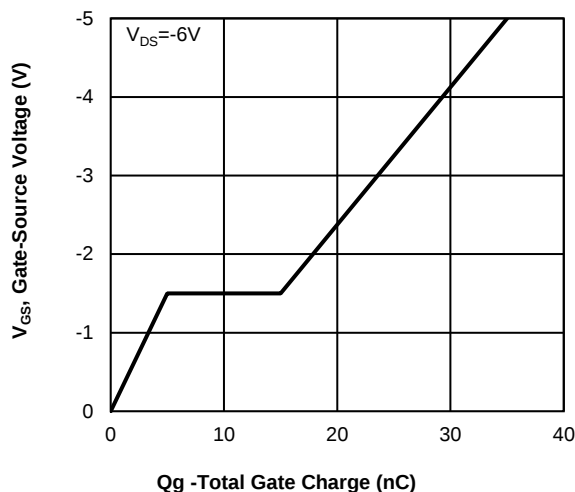


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

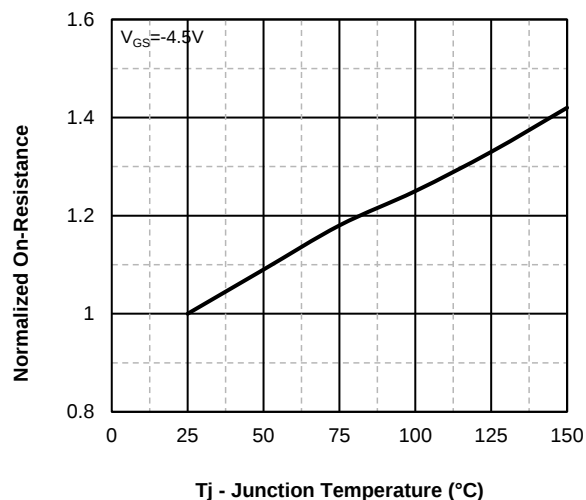


Fig3. Normalized On-Resistance Vs. Temperature

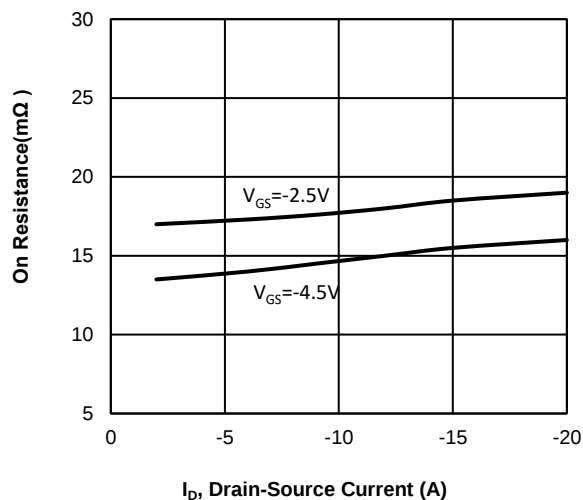


Fig4. On Resistance Vs. Drain-Source Current

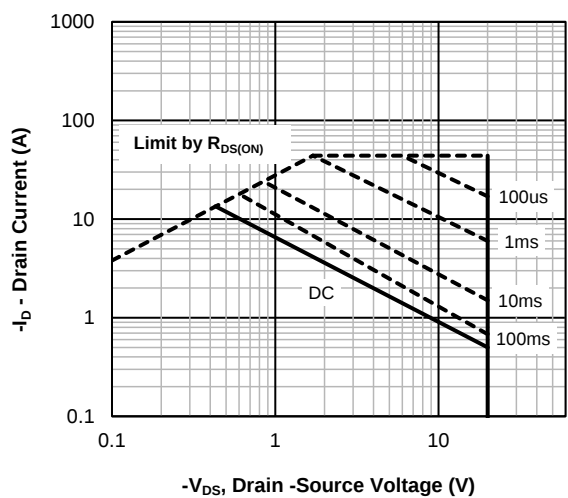


Fig5. Maximum Safe Operating Area

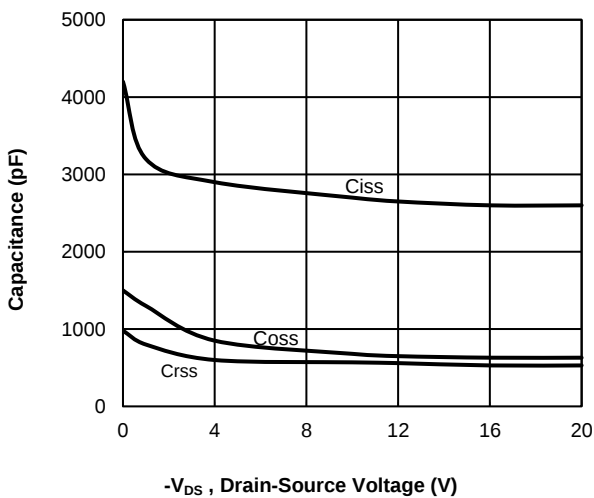
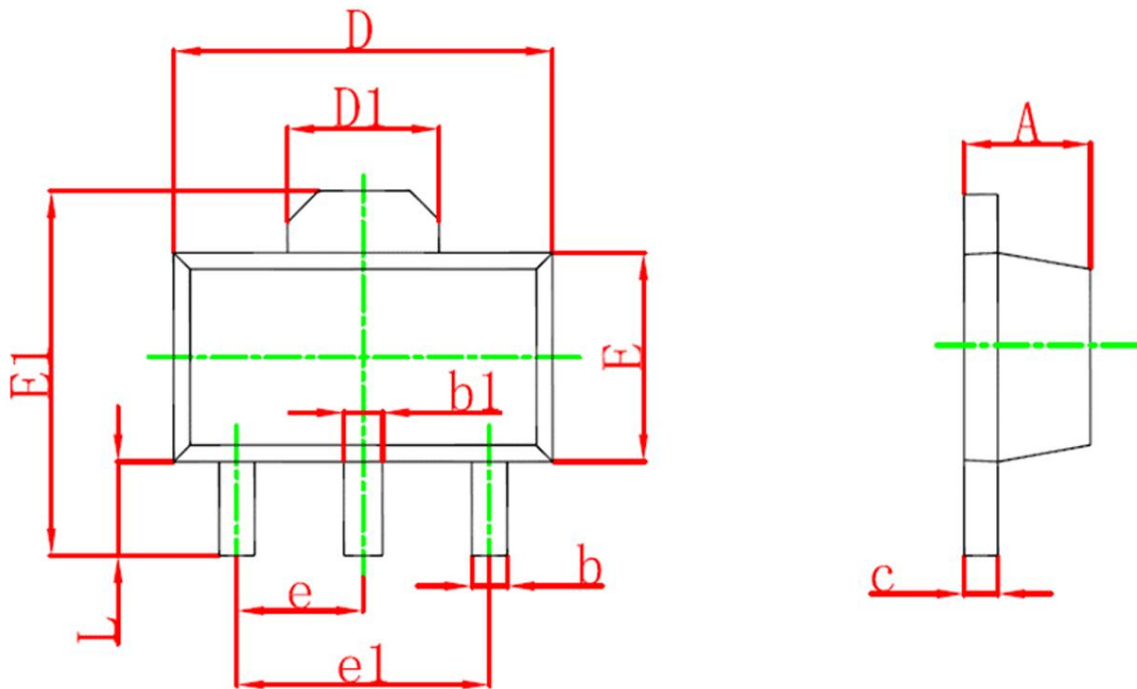


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-89-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060 TYP	
e1	3.000 TYP		0.118 TYP	
L	0.900	1.200	0.035	0.047